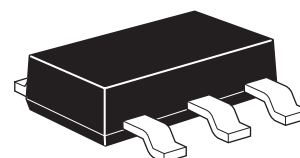


ZXMN6A08G

60V SOT223 N-channel enhancement mode MOSFET

Summary

$V_{(BR)DSS}$	$R_{DS(on)}$ (Ω)	I_D (A)
60	0.080 @ $V_{GS} = 10V$	5.3
	0.150 @ $V_{GS} = 4.5V$	2.8

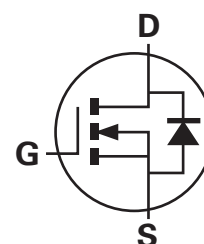


Description

This new generation trench MOSFET from Zetex features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high efficiency power management applications.

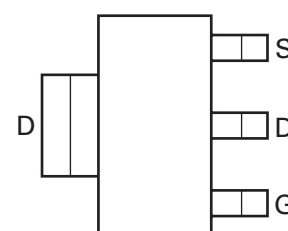
Features

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT223 package



Applications

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control



Pinout - top view

Ordering information

Device	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMN6A08GTA	7	12	1,000
ZXMN6A08GTC	13	12	4,000

Device marking

ZXMN
6A08

ZXMN6A08G

Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain-source voltage	V _{DSS}	60	V
Gate-source voltage	V _{GS}	± 20	V
Continuous drain current @ V _{GS} = 10V; T _{amb} = 25°C ^(b)	I _D	5.3	A
@ V _{GS} = 10V; T _{amb} = 70°C ^(b)		4.2	
@ V _{GS} = 10V; T _{amb} = 25°C ^(a)		3.8	
Pulsed drain current ^(c)	I _{DM}	20	A
Continuous source current (body diode) ^(b)	I _S	2.1	A
Pulsed source current (body diode) ^(c)	I _{SM}	20	A
Power dissipation at T _{amb} = 25°C ^(a)	P _D	2	W
Linear derating factor		16	mW/°C
Power dissipation at T _{amb} = 25°C ^(b)	P _D	3.9	W
Linear derating factor		31	mW/°C
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

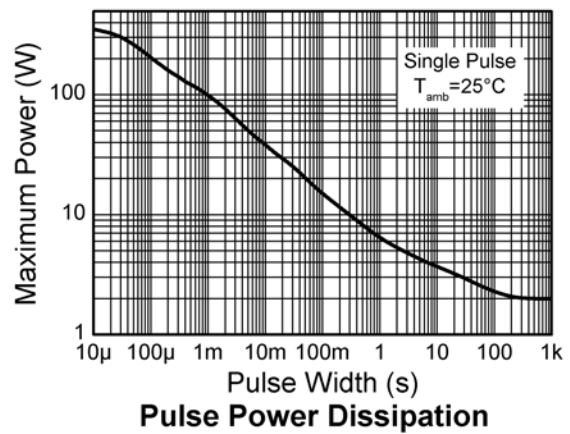
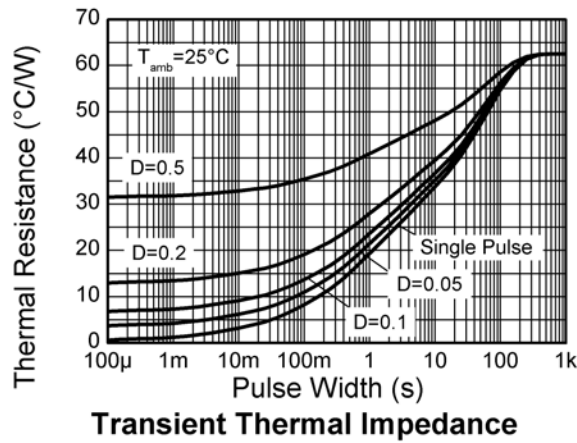
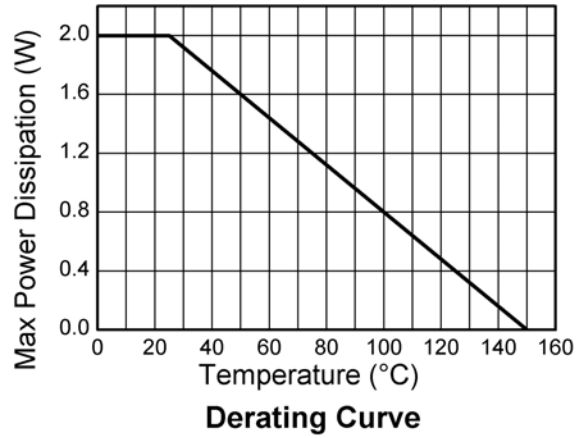
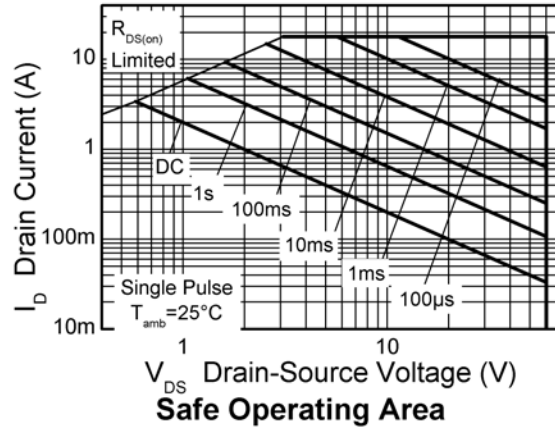
Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\theta JA}$	62.5	$^{\circ}C/W$
Junction to ambient ^(b)	$R_{\theta JA}$	32	$^{\circ}C/W$

NOTES:

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- (b) For a device surface mounted on FR4 PCB measured at $t \leq 10$ sec.
- (c) Repetitive rating - 25mm x 25mm FR4 PCB, $D=0.02$, pulse width 300 μs - pulse width limited by maximum junction temperature.

Typical characteristics



ZXMN6A08G

Electrical characteristics (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Static						
Drain-source breakdown voltage	V _{(BR)DSS}	60			V	I _D = 250μA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}			0.5	μA	V _{DS} = 60V, V _{GS} =0V
Gate-body leakage	I _{GSS}			100	nA	V _{GS} =±20V, V _{DS} =0V
Gate-source threshold voltage	V _{GS(th)}	1			V	I _D = 250μA, V _{DS} =V _{GS}
Static drain-source on-state resistance ^(*)	R _{DS(on)}			0.080	Ω	V _{GS} = 10V, I _D = 4.8A
				0.150	Ω	V _{GS} = 4.5V, I _D = 4.2A
Forward transconductance ^(*) (‡)	g _{fs}		6.6		S	V _{DS} = 15V, I _D = 4.8A
Dynamic ^(‡)						
Input capacitance	C _{iss}		459		pF	V _{DS} = 40V, V _{GS} =0V f=1MHz
Output capacitance	C _{oss}		44.2		pF	
Reverse transfer capacitance	C _{rss}		24.1		pF	
Switching ^(†) (‡)						
Turn-on delay time	t _{d(on)}		2.6		ns	V _{DD} = 30V, I _D = 1.5A R _G ≐6.0Ω, V _{GS} = 10V
Rise time	t _r		2.1		ns	
Turn-off delay time	t _{d(off)}		12.3		ns	
Fall time	t _f		4.6		ns	
Gate charge	Q _g		4.0		nC	V _{DS} = 30V, V _{GS} = 5V I _D = 1.4A
Total gate charge	Q _g		5.8		nC	V _{DS} = 30V, V _{GS} = 10V I _D = 1.4A
Gate-source charge	Q _{gs}		1.4		nC	
Gate drain charge	Q _{gd}		1.9		nC	
Source-drain diode						
Diode forward voltage ^(*)	V _{SD}		0.88	1.2	V	T _j =25°C, I _S = 4A, V _{GS} =0V
Reverse recovery time ^(‡)	t _{rr}		19.2		ns	T _j =25°C, I _S = 1.4A, di/dt=100A/μs
Reverse recovery charge ^(‡)	Q _{rr}		30.3		nC	

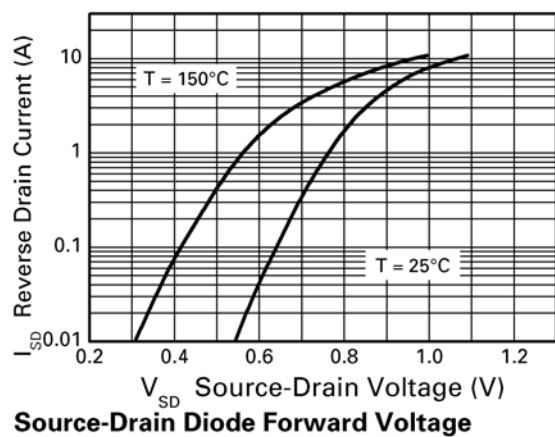
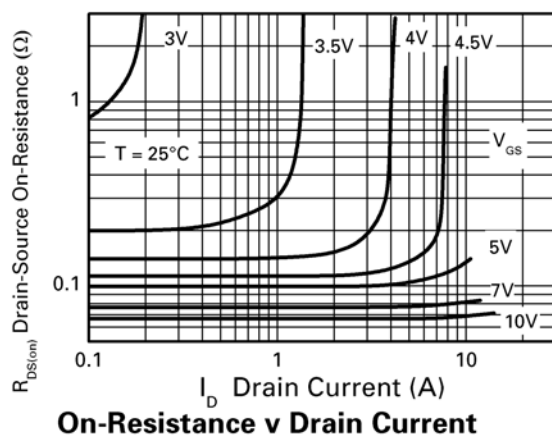
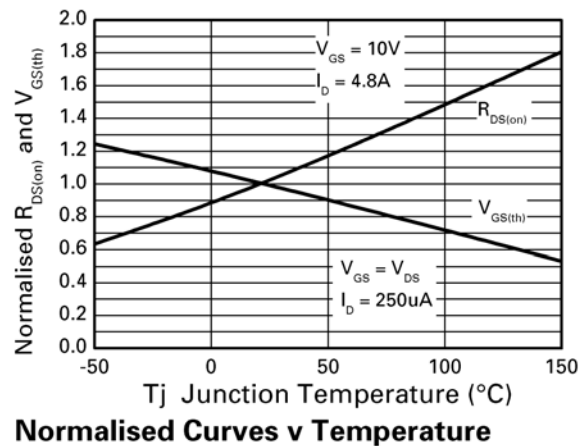
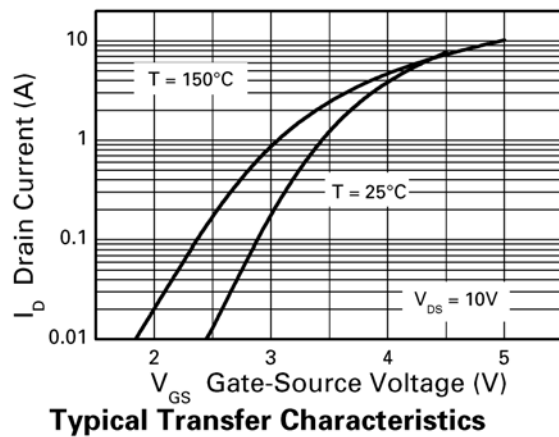
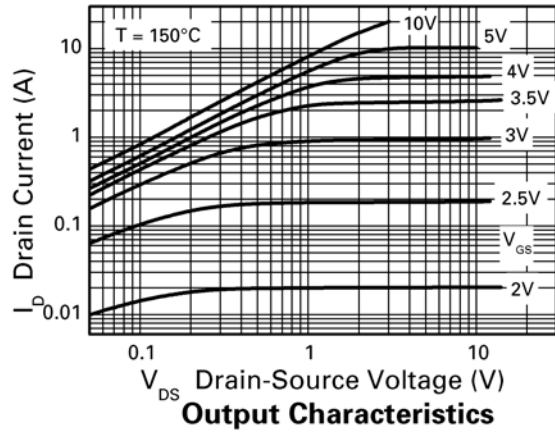
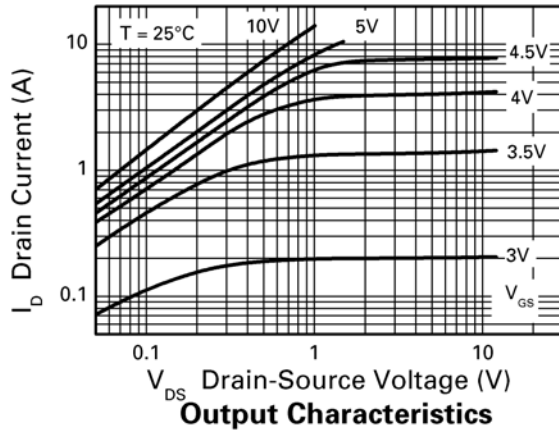
NOTES:

(*) Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$; duty cycle $\leq 2\%$.

(†) Switching characteristics are independent of operating junction temperature.

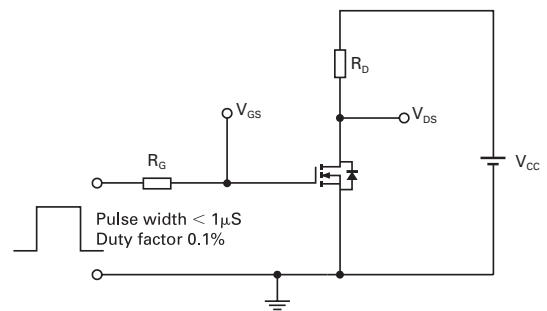
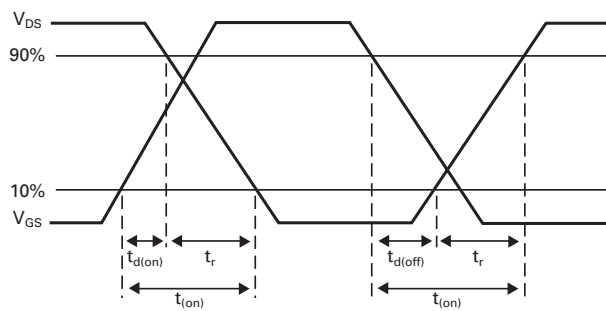
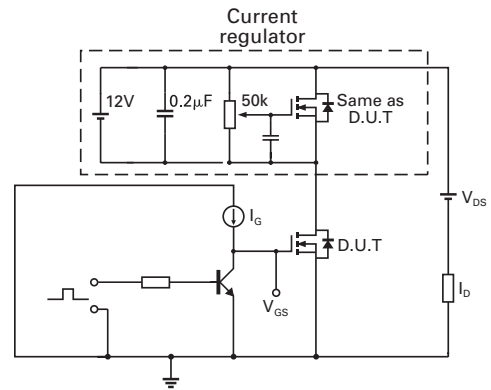
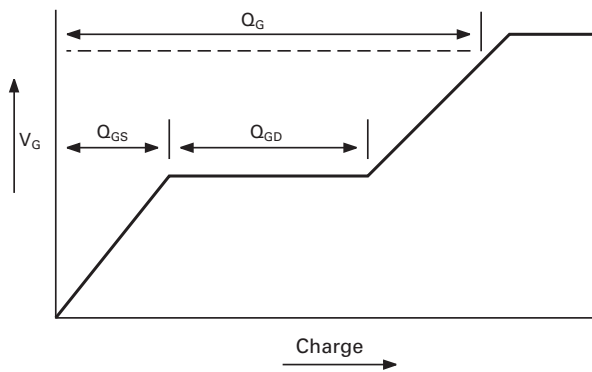
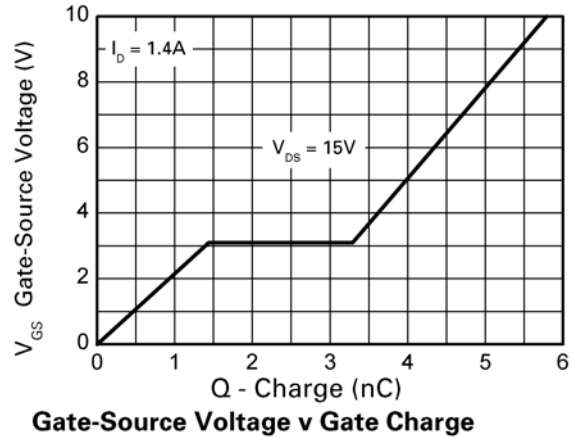
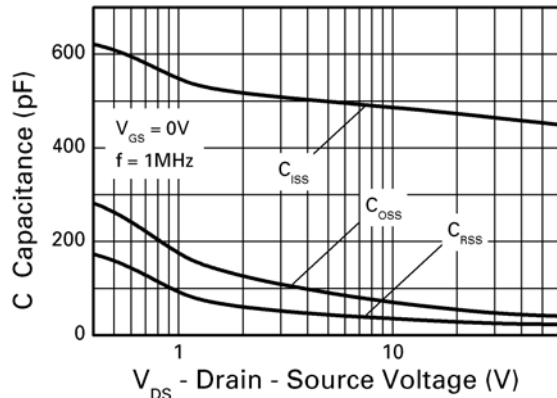
(‡) For design aid only, not subject to production testing.

Typical characteristics



ZXMN6A08G

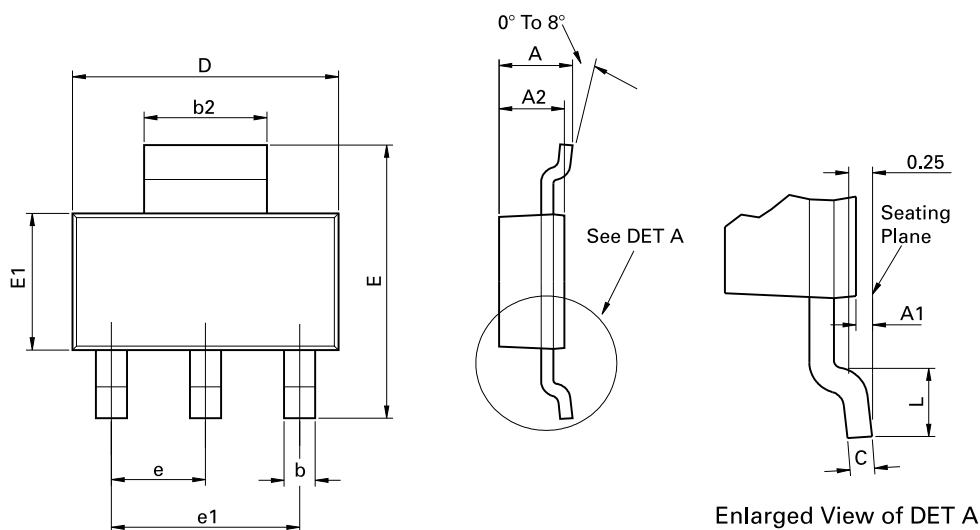
Typical characteristics



ZXMN6A08G

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Package outline - SOT223



Conforms to JEDEC TO-261 AA Issue B

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	-	1.80	-	0.071	e	2.30 BSC		0.0905 BSC	
A1	0.02	0.10	0.0008	0.004	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
C	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-
D	6.30	6.70	0.248	0.264	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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